

DOCKET NO: 250051US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
MITSUHIRO NOGUCHI, ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLN. :
FILED: HEREWITH :
FOR: DATA WRITING METHOD FOR :
SEMICONDUCTOR MEMORY :
DEVICE AND SEMICONDUCTOR :
MEMORY DEVICE :

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 4 of this paper.

Remarks/Arguments begin on page 8 of this paper.